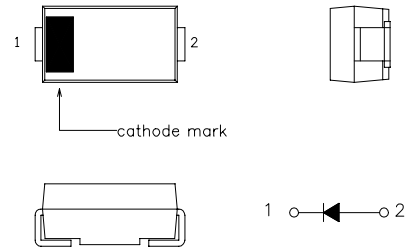


DIODE Type : EC10DS2

FEATURES

- * Miniature Size, Surface Mount Device
- * High Surge Capability
- * Low Forward Voltage Drop
- * Low Reverse Leakage Current
- * Packaged in 12mm Tape and Reel
- * Not Rolling During Assembly

OUTLINE DRAWING



Maximum Ratings

Approx Net Weight:0.06g

Rating	Symbol	EC10DS2		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	200		V
Non-repetitive Peak Reverse Voltage	V_{RSM}	400		V
Average Rectified Output Current	I_O	0.74	Ta=25 °C *1	50Hz Half Sine Wave Resistive Load
		1.0	Ta=25 °C *2	
RMS Forward Current	$I_{F(RMS)}$	1.57		A
Surge Forward Current	I_{FSM}	25	50Hz Half Sine Wave, 1cycle Non-repetitive	A
Operating Junction Temperature Range	T_{jw}	-40 to +150		°C
Storage Temperature Range	T_{stg}	-40 to +150		°C

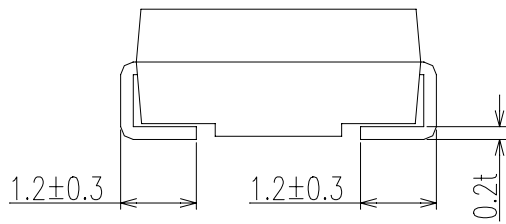
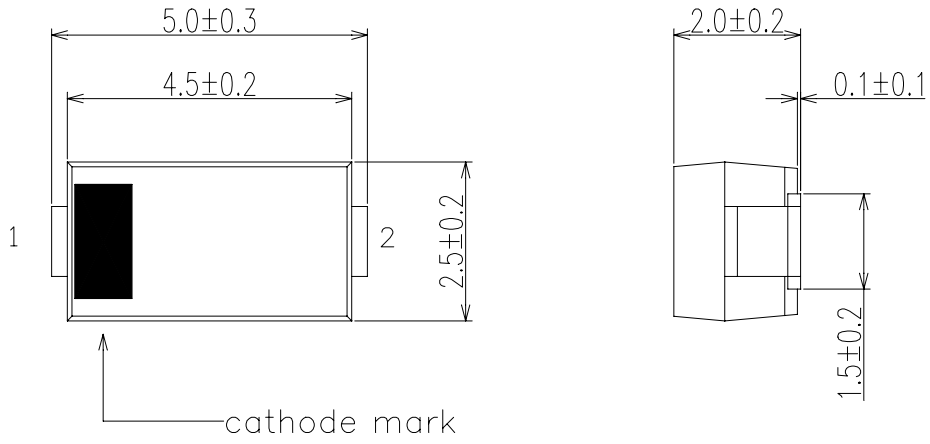
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Peak Reverse Current	I_{RM}	$T_j = 25^\circ\text{C}$, $V_{RM} = V_{RRM}$	-	-	10	μA	
Peak Forward Voltage	V_{FM}	$T_j = 25^\circ\text{C}$, $I_{FM} = 1.0\text{A}$	-	-	1.1	V	
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	*1	-	-	157	°C /W
			*2	-	-	108	

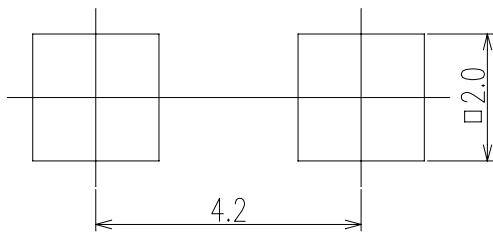
*1 Glass Epoxy Substrate Mounted (Soldering Lands=2x2mm, Both Sides)

*2 Alumina Substrate Mounted (Soldering Lands=2x2mm, Both Sides)

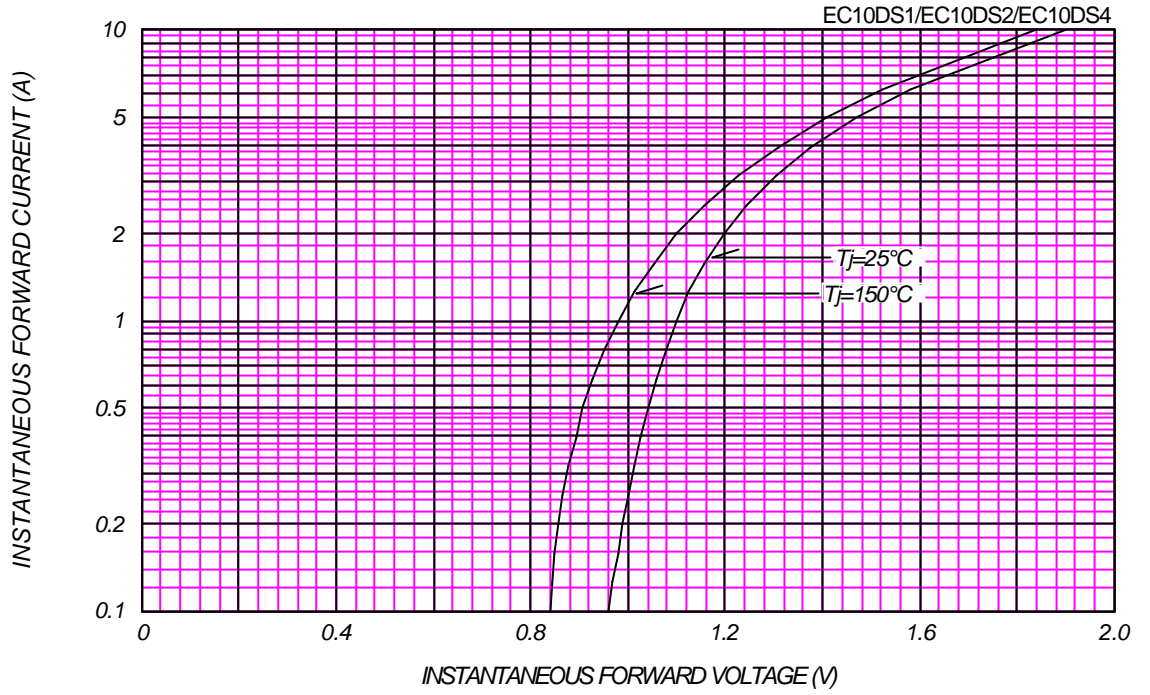
EC10D*_ OUTLINE DRAWING (Dimensions in mm)



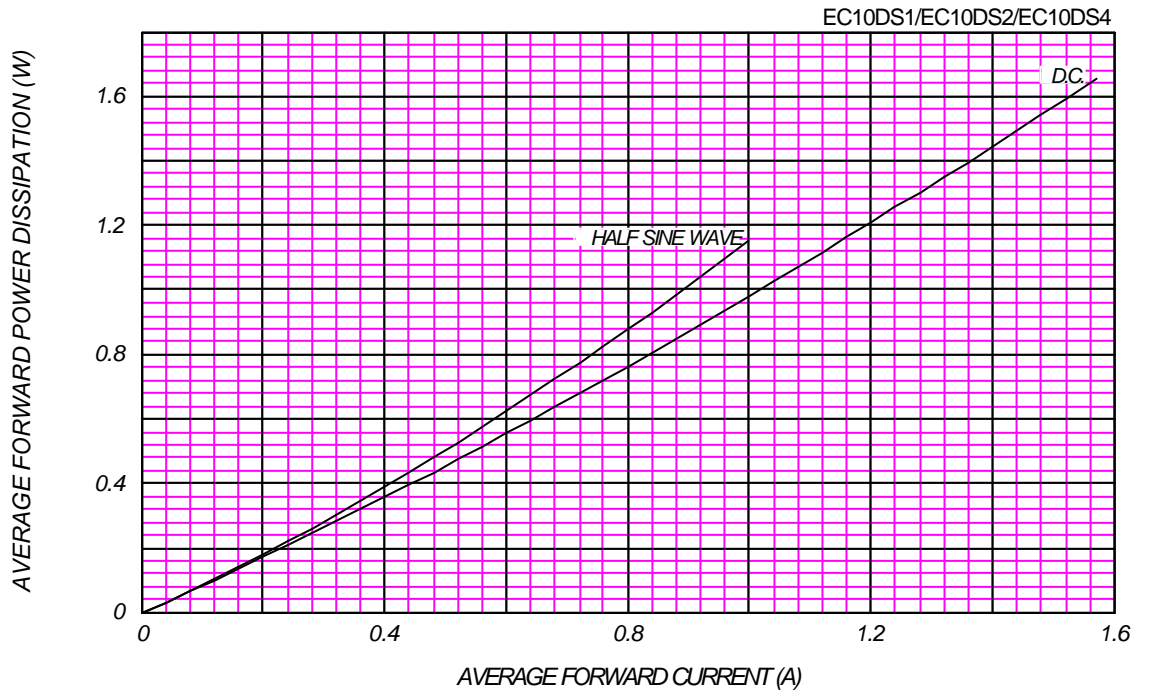
SOLDERING PAD



FORWARD CURRENT VS. VOLTAGE



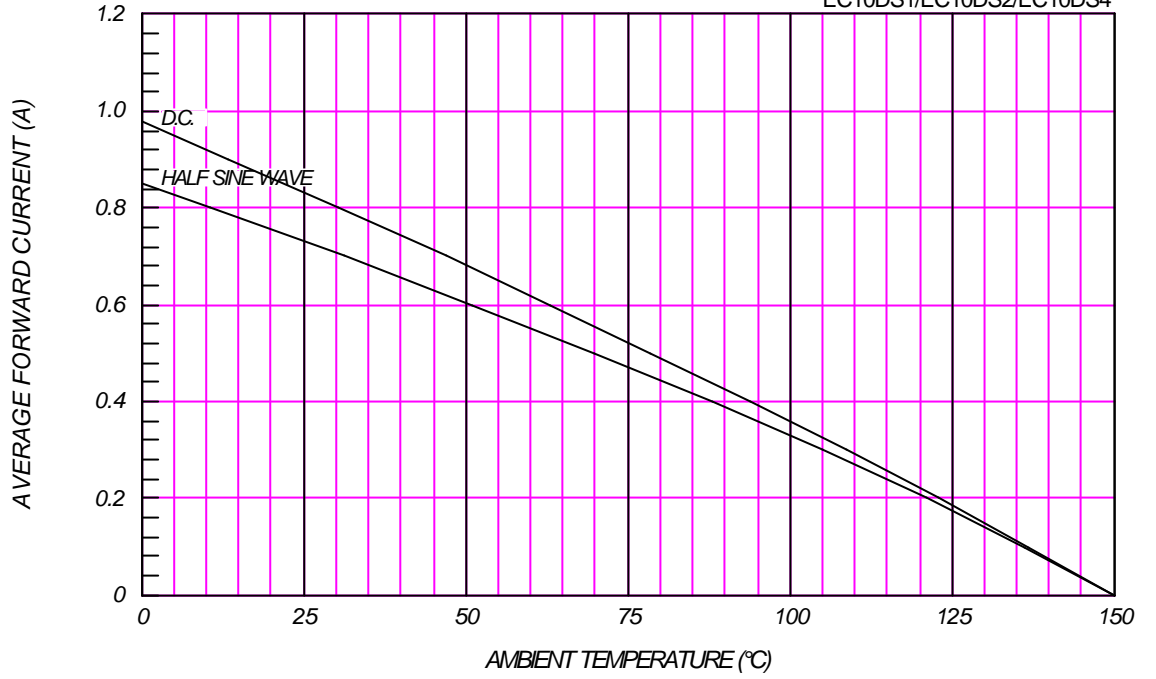
AVERAGE FORWARD POWER DISSIPATION



AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

Glass-Epoxy Substrate Mounted(Soldering Land=2x2mm)

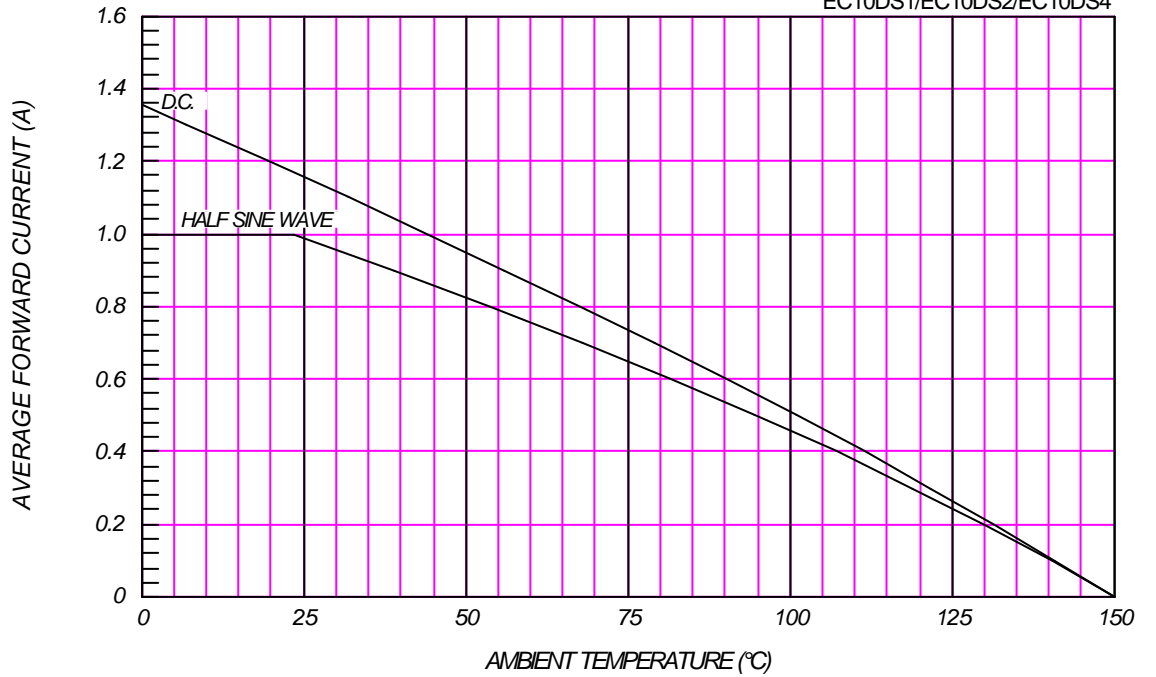
EC10DS1/EC10DS2/EC10DS4



AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

Alumina Substrate Mounted(Soldering Land=2x2mm)

EC10DS1/EC10DS2/EC10DS4



SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

EC10DS1/EC10DS2/EC10DS4

